

# OPA8512HP

High Speed

# Infrared LED Chip

GaAlAs/GaAlAs

**1. Material** Substrate GaAlAs (N Type) Removed  
Epitaxial Layer GaAlAs (P/N Type)

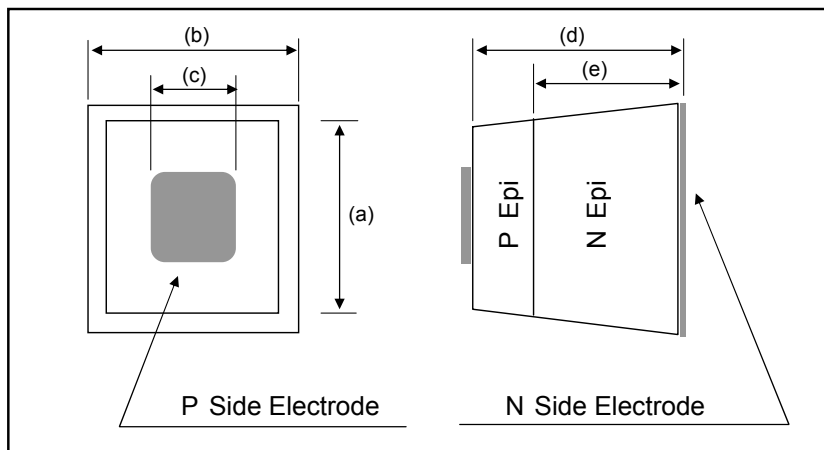
**2. Electrode** N(Cathode) Side Gold Alloy  
P(Anode) Side Gold Alloy

**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.6	2	V	IF=50mA
Reverse Voltage	$V_R$	5			V	IR=10uA
Power	$P_O$	13	17		mW	IF=50mA
Wavelength	$\lambda_P$		850		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	$T_r$		25		ns	
Fall Time	$T_f$		13		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

- 4. Mechanical Data**
- (a) Emission Area ----- 11.6mil x 11.6mil
  - (b) Bottom Area ----- 12.6mil x 12.6mil
  - (c) Bonding Pad ----- 130um
  - (d) Chip Thickness ----- 7mil
  - (e) Junction Height ----- 5.7mil



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